MSKSEMI 美森科













ESD

VS

TSS

MOV

GDT

PIFD

AU0511P1-MS

Product specification





Features

- Capacitance:3.5pF(typ.)
- ReverseWorkingVoltage:5V
- IEC61000-4-2(ESDAir):±25KV
- IEC61000-4-2(ESDContact):±20KV
- IEC61000-4-5(Lightning8/20μs):2.5A

Applications

- Cellularphones
- Portabledevices
- Digitalcameras
- Powersupplies

Reference News

PACKAGE OUTLINE	PIN Configuration	Marking		
		AN		
DFN1006				

Limiting Values(TA = 25 °C, unless otherwise specified)

Symbol	Parameter Conditions		Min	Max	Unit
Vesd	Electrostatic Discharge Voltage	IEC 61000-4-2; Contact Discharge	-	±20	kV
		IEC 61000-4-2; Air Discharge	-	±25	kV
P _{PP}	Peak Pulse Power	t _P = 8/20 μs	-	40	W
ІРРМ	Rated Peak Pulse Current	t _P = 8/20 μs	-	2.5	Α
TA	Ambient Temperature Range	-	-55	150	°C
Tstg	Storage Temperature Range	-	-55	150	°C

Electrical Characteristics(TA = 25 °C, unless otherwise specified)

Symbol	Parameter	Conditions	Min	Тур.	Max	Unit
VRWM	Reverse Working Voltage	T _A = 25 °C	-	-	5.0	V
V _{BR}	Breakdown Voltage	I _R = 1mA; T _A = 25 °C	5.6	-	9.0	V
l _R	Reverse Leakage Current	V _{RWM} = 5V; T _A = 25 °C	-	-	100	nA
Vc	Clamping Voltage	I _{PP} = 1A, t _P =8/20µs	-	-	13	V
		I _{PP} =2.5A, t _P =8/20µs	-	-	16	V
CJ	Junction Capacitance	V _R = 0V, f = 1 MHz	-	3.5	4.0	pF



TypicalCharacteristics

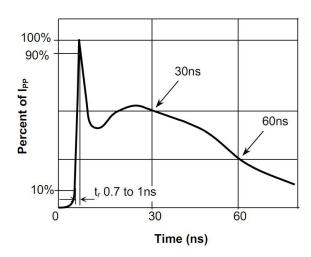


Fig.1 Pulse Waveform-ESD (IEC61000-4-2)

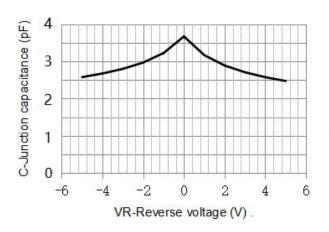


Fig.3 Capacitance vs. Reveres Voltage

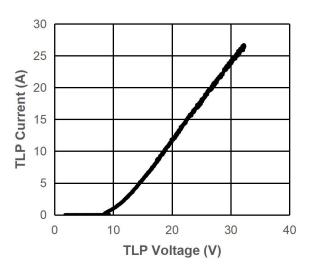


Fig.2 Transmission Line Pulse (TLP)

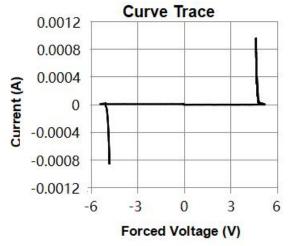
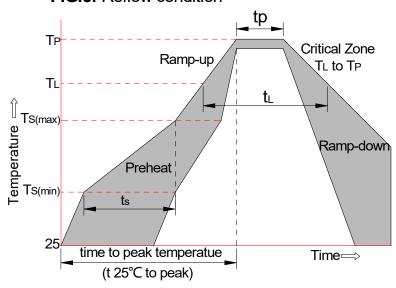


Fig.4 IV Curve (Forward Voltage)



SolderingParameters

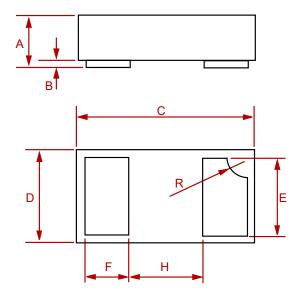
FIG.5: Reflow condition



	Reflow Condition	Pb-Free Assembly	
Pre-heat	-Temperature Min (T _{s(min)})	+150°C	
	-Temperature Max(T _{s(max)})	+200°C	
	-Time (Min to Max) (ts)	60-180 secs.	
Average ramp up rate (Liquid us Temp (T _L) to peak)		3°C/sec. Max	
T _{s(max)} to T _L - Ramp-up Rate		3°C/sec. Max	
Reflow	-Temperature(T _L)(Liquid us)	+217°C	
	-Temperature(t _L)	60-150 secs.	
Peak Temp (T _p)		+260(+0/-5)°C	
Time within 5°C of actual Peak Temp (t _p)		30 secs. Max	
Ramp-down Rate		6°C/sec. Max	
xTime 25°C to Peak Temp (T _P)		8 min. Max	
Do not exceed		+260°C	

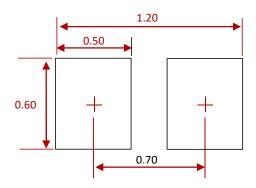


PACKAGE MECHANICAL DATA



Dim	Inches		Millimeters	
	MIN	MAX	MIN	MAX
А	0.0125	0.02	0.32	0.52
В	0.000	0.002	0.00	0.05
С	0.037	0.043	0.95	1.080
D	0.022	0.027	0.55	0.680
E	0.016	0.024	0.40	0.60
F	0.008	0.012	0.20	0.30
Н	0.015Typ.		0.40	Тур.
R	0.001	0.005	0.05	0.15

Suggested Pad Layout



NOTES:

- 1. CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
- 2. THIS LAND PATTERN IS FOR REFERENCE PURPOSES ONLY. CONSULT YOUR MANUFACTURING GROUP TO ENSURE YOUR COMPANY'S MANUFACTURING GUIDELINES ARE MET.

REEL SPECIFICATION

P/N	PKG	QTY
AU0511P1-MS	DFN1006	10000



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